

SuperSOT4™ 50V NPN SILICON LOW SATURATION SWITCHING TRANSISTOR

SUMMARY

$V_{CE0}=50V$; $R_{SAT} = 17m\Omega$; $I_C= 6A$

DESCRIPTION

This new 4th generation ultra low saturation transistor utilises the Zetex matrix structure combined with advanced assembly techniques to give extremely low on state losses. This makes it ideal for high efficiency, low voltage switching applications.

FEATURES

- Extremely Low Equivalent On Resistance
- Extremely Low Saturation Voltage
- h_{FE} characterised up to 12A
- $I_C=6A$ Continuous Collector Current
- MSOP8 package

APPLICATIONS

- DC - DC Converters
- Power Management Functions
- Power switches
- Motor control

ORDERING INFORMATION

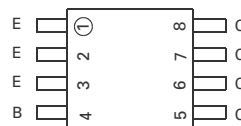
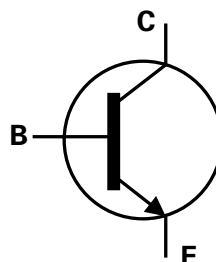
DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXT14N50DXTA	7	12mm embossed	1000 units
ZXT14N50DXTC	13	12mm embossed	4000 units

DEVICE MARKING

T14N50DX



MSOP8



Top View

ZXT14N50DX

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	7.5	V
Peak Pulse Current (c)	I_{CM}	15	A
Continuous Collector Current	I_C	6	A
Base Current	I_B	500	mA
Power Dissipation at $T_A=25^{\circ}\text{C}$ (a) Linear Derating Factor	P_D	1.1 8.8	W mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ (b) Linear Derating Factor	P_D	1.8 14.4	W mW/ $^{\circ}\text{C}$
Operating and Storage Temperature Range	$T_J:T_{stg}$	-55 to +150	$^{\circ}\text{C}$

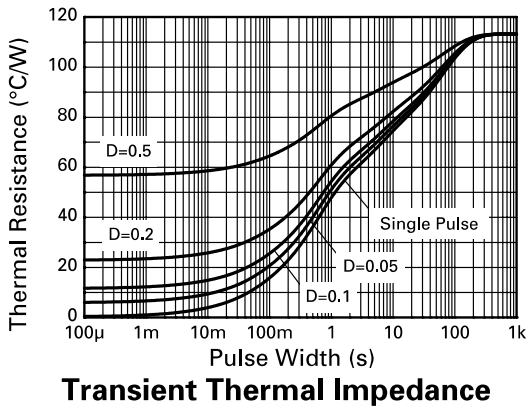
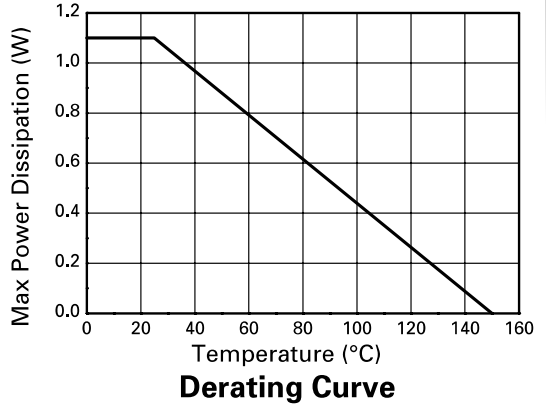
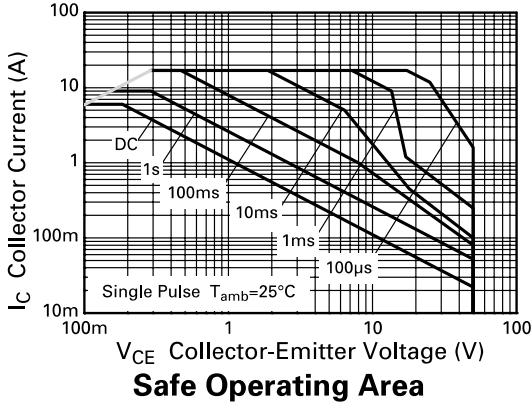
THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	113	$^{\circ}\text{C/W}$
Junction to Ambient (b)	$R_{\theta JA}$	70	$^{\circ}\text{C/W}$

NOTES

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
- (b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ secs.
- (c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

CHARACTERISTICS



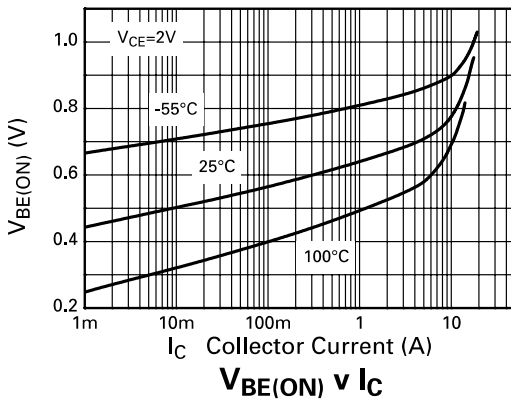
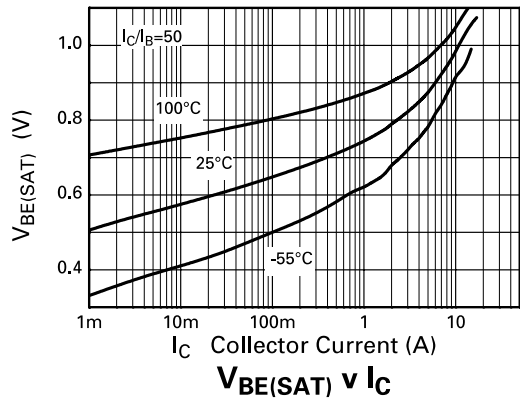
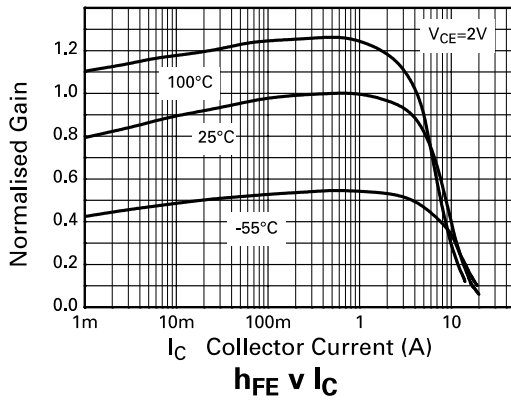
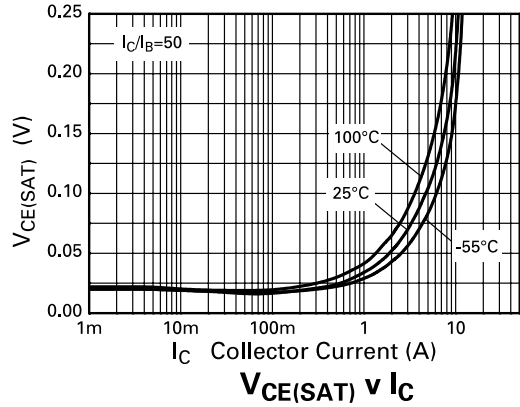
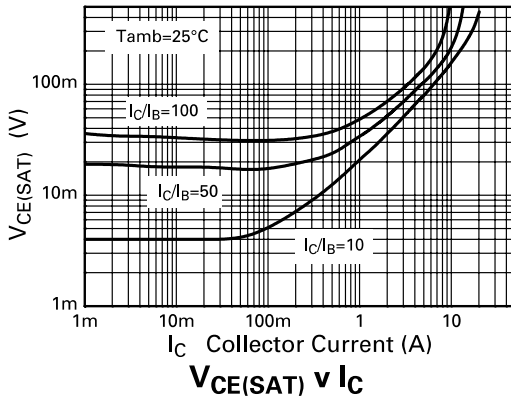
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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	100	190		V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	50	70		V	$I_C = 10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	7.5	8.5		V	$I_E = 100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			100	nA	$V_{CB} = 80\text{V}$
Emitter Cut-Off Current	I_{EBO}			100	nA	$V_{EB} = 6\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			100	nA	$V_{CES} = 80\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		6 50 90 120 100	9 70 120 155 130	mV mV mV mV mV	$I_C = 0.1\text{A}, I_B = 10\text{mA}^*$ $I_C = 1\text{A}, I_B = 10\text{mA}^*$ $I_C = 3\text{A}, I_B = 40\text{mA}^*$ $I_C = 6\text{A}, I_B = 120\text{mA}^*$ $I_C = 6\text{A}, I_B = 300\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			0.95	V	$I_C = 6\text{A}, I_B = 120\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			0.90	V	$I_C = 6\text{A}, V_{CE} = 2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	250 300 200 75	400 450 350 150	900		$I_C = 10\text{mA}, V_{CE} = 2\text{V}^*$ $I_C = 1\text{A}, V_{CE} = 2\text{V}^*$ $I_C = 6\text{A}, V_{CE} = 2\text{V}^*$ $I_C = 12\text{A}, V_{CE} = 2\text{V}^*$
Transition Frequency	f_T		185		MHz	$I_C = 300\text{mA}, V_{CE} = 10\text{V}$ $f = 30\text{MHz}$
Output Capacitance	C_{obo}		65		pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$
Turn-On Time	$t_{(on)}$		210		ns	$V_{CC} = 10\text{V}, I_C = 5\text{A}$ $I_{B1} = I_{B2} = 125\text{mA}$
Turn-Off Time	$t_{(off)}$		740		ns	

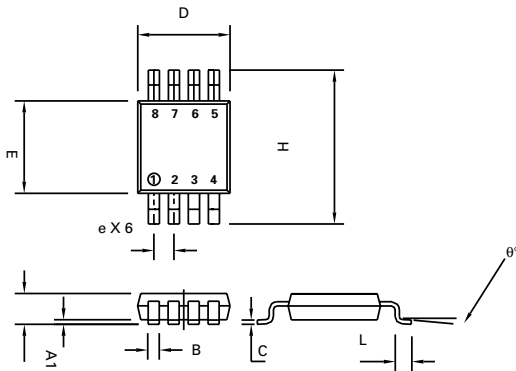
*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS



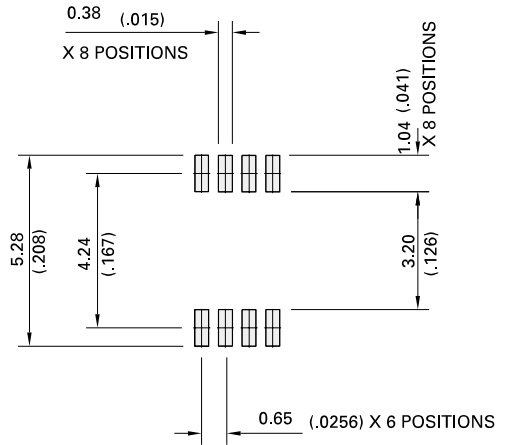
ZXT14N50DX

PACKAGE DIMENSIONS



Conforms to JEDEC MO-187 Iss A

PAD LAYOUT DETAILS



DIM	Millimetres		Inches	
	MIN	MAX	MIN	MAX
A		1.10		0.043
A1	0.05	0.15	0.002	0.006
B	0.25	0.40	0.010	0.016
C	0.13	0.23	0.005	0.009
D	2.90	3.10	0.114	0.122
e	0.65	BSC	0.0256	BSC
E	2.90	3.10	0.114	0.122
H	4.90	BSC	0.193	BSC
L	0.40	0.70	0.016	0.028
q°	0°	6°	0°	6°



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